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BOX A/P

IN THE UNITED STATES PATENT AND TRADE MARKS OFFICE

Applicant: R.C. Foss et al

11/a(N)
(E)

Serial No: 07/680,747

FJ

Filed: April 5, 1991

10-25-93

Title: METHOD FOR DRAM SENSING CURRENT CONTROL

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Art Unit: 2502

OCT 25 1995

Examiner: T. Dinh

GROUP 2000

Our File: 628.30050X00

The Commissioner of Patents
and Trade Marks,
Washington, D.C., 20231
U.S.A.

October 18, 1993

Dear Sir:

This is in response to the official action dated May 17th, 1993 in the above-identified application.

Please amend the claims as follows:

1. (Amended) A dynamic random access memory (DRAM) comprising:
 - (a) a plurality of bit storage capacitors,
 - (b) a folded bit line comprised of a complementary bit line pair for receiving charge stored on one of said capacitors, having bit line capacitance,
 - (c) a sense amplifier having a pair of sense nodes for sensing a voltage differential across said sense nodes,
 - (d) high resistance controllable current leakage
imperfect isolating means connecting said bit line to said

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